



2N6426



NPN Darlington Transistor

This device is designed for applications requiring extremely high current gain at currents to 1.0 A. Sourced from Process 05. See MPSA14 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	12	V
I _C	Collector Current - Continuous	1.2	A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted				
Symbol	Characteristic	Мах	Units	
		2N6426		
PD	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W	
R _{θJA}	Thermal Resistance, Junction to Ambient	200	°C/W	

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Electrical Characteristics TA = 25°C unless otherwise noted						
ymbol	Parameter	Test Conditions	Min	Мах	Units	
FF CHA	RACTERISTICS					
R)CEO	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	40		V	
R)CBO	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	40		V	
R)EBO	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$	12		V	
)	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, \text{ I}_{E} = 0$		50	nA	
)	Collector Cutoff Current	$V_{CE} = 25 V, I_{B} = 0$		1.0	μΑ	
	Emitter Cutoff Current	$V_{EB} = 10 \text{ V}, I_{C} = 0$		50	nA	

ON CHARACTERISTICS*

 $V_{(BR)CEO}$ V_{(BR)CBO}

V_{(BR)EBO}

 I_{CBO}

 \mathbf{I}_{CEO}

 I_{EBO}

h _{FE}	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$	20,000	200,000	
		$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \text{ mA}$	30,000	300,000	
		$V_{CE} = 5.0 \text{ V}, I_{C} = 500 \text{ mA}$	20,000	200,000	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 50$ mA, $I_{\rm B} = 0.5$ mA		1.2	V
		$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		2.0	V
V _{BE(on)}	Base-Emitter On Voltage	$I_{C} = 50 \text{ mA}, V_{CE} = 5.0 \text{ V}$		1.75	V

SMALL SIGNAL CHARACTERISTICS

Cob	Output Capacitance	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1.0 \text{ MHz}$		7.0	pF
C _{ib}	Input Capacitance	$V_{EB} = 1.0 \text{ V}, I_{C} = 0, f = 1.0 \text{ MHz}$		15	pF
h _{fe}	Small-Signal Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$	20,000		
h _{ie}	Input Impedance	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$	100	2,000	kΩ
h _{oe}	Output Admittance	f = 1.0 kHz		1,000	μmho
NF	Noise Figure	$I_{c} = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $R_{s} = 100 \text{ k}\Omega,$ $f = 10 \text{ kHz to 15.7 \text{ kHz}}$		10	dB

*Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%



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